Form PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTORNEY DOCKET NO. MI22-2308

SERIAL NO. 10/615,051

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APPLICANT: Brian A. Vaartstra

FILING DATE 7/7/2003

GROUP ART UNIT 2823

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
BU	AA	6,013,583	1/11/2000	Ajmera et al.			
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FOREIGN PAT	ENT D	OCUMENTS	:					
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BN	AI	EP 0817251 A	1/1998	EPO				
•	AJ							

OTHER REFE	RENCE	S (including Author, Title, Date, Pertinent Pages, Etc.)
	AK	PCT/US2004/021156; Filed 6/30/2004; Search Report.
Bu		
		PCT/US2004/021156; Filed 6/30/2004; Written Opinion Issued on 1/18/2005; 6 pps.
BU	AL	
EXAMINER BOOK	K	DATE CONSIDERED 2 heale 7/5/2005

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FOREIGN P	ATENT	DOCUMENTS						
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